Low-Voltage Circuits in Floating-Gate and Double-Gate CMOS

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Mixed Analog-Digital VLSI Circuits and Systems Lab

- **Research focus**: Low-voltage/low-power analog and mixed-signal circuit design
- Current M.S./Ph.D. students: Abhishek Kammula, Eric McDonald, Kofi Odame, Sheng-Yu Peng
- Former M.S./Ph.D. students: Karan Mathur, Mark Neidengard, Yuan Yang
- Current projects:
 - High-level synthesis of translinear and log-domain circuits and systems
 - Floating-gate MOS (FGMOS) circuit design
 - Double-gate MOS (DGMOS) modelling and circuit design
 - Chemical sensing with chemoreceiptive neuron MOS ($C\nu$ MOS) transistors





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- By programming Q, we can arrange that $V \approx V_{\text{DSsat}}$ for any given value of I_{b} .
- This form has the simplicity of Säckinger's original, but it also has a wide output swing.
- Not robust to drift in Q, or changes in I_b or temperature.

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- How can we set V_b to make $V \approx V_{DSsat}$? Use indirect negative feedback!
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- One V_b generator can be shared by multiple regulated cascodes.

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- Requires independent access to front and back gates.
- Requires that the front and back gate voltages affect the channel current in a (qualitatively) symmetric manner.
- Desirable for the threshold voltages of the front and back gates to both be positive.





